



### **PDTD114ETVL Information**



For Reference Only

Part Number PDTD114ETVL
Manufacturer Nexperia USA Inc.

**Category** Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Single, Pre-Biased

**Description**TRANS PREBIAS NPN 0.425W**Package**TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## **PDTD114ETVL Specifications**

Manufacturer Part Number  Manufacturer  Nexperia USA Inc.  Discrete Semiconductor Products  Transistors - Bipolar (BJT) - Single, Pre-Biased  Package  TO-236-3, SC-59, SOT-23-3  Series  - Transistor Type  NPN - Pre-Biased  Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  Vee Saturation (Max) @ Ib, Ic  Current - Collector Cutoff (Max)  Frequency - Transition  Package  Discrete Semiconductor Products  Transistors - Bipolar (BJT) - Single, Pre-Biased  DO-236-3, SC-59, SOT-23-3  Series  - TO-236-3, SC-59, SOT-23-3  Series  - To-246-3, SC-59, SOT-23-3  Series  - To-246-4, Ser
Category  Discrete Semiconductor Products  Transistors - Bipolar (BJT) - Single, Pre-Biased  Package  TO-236-3, SC-59, SOT-23-3  Series  - Transistor Type  NPN - Pre-Biased  Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  Vce Saturation (Max) @ Ib, Ic  100mV @ 2.5mA, 50mA  Current - Collector Cutoff (Max)  Frequency - Transition  Discrete Semiconductor Products  Transistors - Bipolar (BJT) - Single, Pre-Biased  10-236-3, SC-59, SOT-23-3  - 100mA  500mA  500mA  500mA  500mA  500mA
Transistors - Bipolar (BJT) - Single, Pre-Biased TO-236-3, SC-59, SOT-23-3 Series - Transistor Type NPN - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition  Transistors - Bipolar (BJT) - Single, Pre-Biased TO-236-3, SC-59, SOT-23-3  -  100mV e Pre-Biased  500mA  500mA  500mA  500mA  500mA  500mA  500mA
Package TO-236-3, SC-59, SOT-23-3 Series - Transistor Type NPN - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition  TO-236-3, SC-59, SOT-23-3  - TO SOMA  - TO Washing the second of the secon
Series  Transistor Type  NPN - Pre-Biased  Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  Vce Saturation (Max) @ Ib, Ic  Current - Collector Cutoff (Max)  Frequency - Transition  NPN - Pre-Biased  NPN - Pre-Biased  500mA  500  10k  10k  10k  10k  70 @ 50mA, 5V  Vce Saturation (Max) @ Ib, Ic  100mV @ 2.5mA, 50mA  500nA
Transistor Type  Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  Vce Saturation (Max) @ Ib, Ic  Current - Collector Cutoff (Max)  Frequency - Transition  NPN - Pre-Biased  500mA  500mA  10k  10k  10k  10k  70 @ 50mA, 5V  100mV @ 2.5mA, 50mA  500nA
Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  Vce Saturation (Max) @ Ib, Ic  Current - Collector Cutoff (Max)  Frequency - Transition  500mA  50V  10k  10k  70 @ 50mA, 5V  100mV @ 2.5mA, 50mA  500nA
Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  70 @ 50mA, 5V  Vce Saturation (Max) @ Ib, Ic  100mV @ 2.5mA, 50mA  Current - Collector Cutoff (Max)  Frequency - Transition  50V  10k  70 @ 50mA, 5V  225MHz
Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  70 @ 50mA, 5V  Vce Saturation (Max) @ Ib, Ic  100mV @ 2.5mA, 50mA  Current - Collector Cutoff (Max)  Frequency - Transition  225MHz
Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  70 @ 50mA, 5V  Vce Saturation (Max) @ Ib, Ic  100mV @ 2.5mA, 50mA  Current - Collector Cutoff (Max)  Frequency - Transition  225MHz
DC Current Gain (hFE) (Min) @ Ic, Vce  70 @ 50mA, 5V  Vce Saturation (Max) @ Ib, Ic  100mV @ 2.5mA, 50mA  Current - Collector Cutoff (Max)  Frequency - Transition  225MHz
Vce Saturation (Max) @ Ib, Ic100mV @ 2.5mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition225MHz
Current - Collector Cutoff (Max) 500nA Frequency - Transition 225MHz
Frequency - Transition 225MHz
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Power - Max 320mW
Mounting Type Surface Mount
Package / Case TO-236-3, SC-59, SOT-23-3
Supplier Device Package TO-236AB (SOT23)
Report errors?

#### **PDTD114ETVL Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# PDTD114ETVL Payment Methods





















## PDTD114ETVL Shipping Methods













If you have any question about PDTD114ETVL, please do not hesitate to contact us!

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